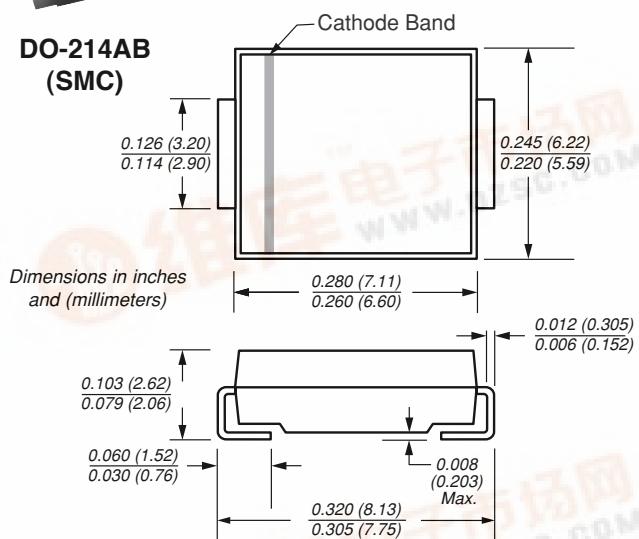




查询SS3H10供应商

捷多邦，专业PCB打样工厂，24小时加急出货

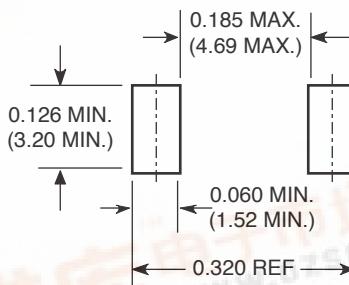
DO-214AB
(SMC)

New Product

SS3H9 and SS3H10

Vishay Semiconductors
formerly General SemiconductorHigh Voltage Surface Mount
Schottky Barrier RectifiersReverse Voltage 90 to 100V
Forward Current 3.0A

Mounting Pad Layout



Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Low profile surface mount package
- Built-in strain relief
- Low power loss, high efficiency
- For use in low voltage high frequency inverters, free wheeling, and polarity protection applications
- Guardring for overvoltage protection
- High temperature soldering guaranteed: 250°C/10 seconds at terminals

Mechanical Data

Case: JEDEC DO-214AB molded plastic body**Terminals:** Solder plated, solderable per MIL-STD750, Method 2026**Polarity:** Color band denotes cathode end**Weight:** 0.007 oz., 0.25 gMaximum Ratings and Thermal Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | SS3H9 | SS3H10 | Unit |
|--|------------------------------------|-------------|--------|------|
| Device marking code | | MS9 | MS10 | |
| Maximum repetitive peak reverse voltage | V_{RRM} | 90 | 100 | V |
| Working peak reverse voltage | V_{RWM} | 90 | 100 | V |
| Maximum DC blocking voltage | V_{DC} | 90 | 100 | V |
| Maximum average forward rectified current at: $T_L = 115^\circ\text{C}$ | $I_{F(AV)}$ | 3.0 | | |
| Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) | I_{FSM} | 100 | | |
| Peak repetitive reverse surge current at $t_p = 2.0\mu\text{s}$, 1KHz | I_{RRM} | 1.0 | | |
| Critical rate of rise of reverse voltage | dv/dt | 10,000 | | |
| Typical thermal resistance – junction to lead $T_L = 25^\circ\text{C}$ – junction to ambient ⁽²⁾ | $R_{\theta JL}$ $R_{\theta JA}$ | 9.7 32 | | |
| Operating junction and storage temperature range | T_J , T_{STG} | −65 to +175 | | |

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| | | | | |
|--|---|-------|-------------|---------------------|
| Maximum instantaneous forward voltage at: ⁽¹⁾ | $I_F = 3.0\text{A}$, $T_J = 25^\circ\text{C}$ $I_F = 3.0\text{A}$, $T_J = 125^\circ\text{C}$ | V_F | 0.8 0.65 | V |
| Maximum DC reverse current at rated DC blocking voltage | $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$ | I_R | 20 4 | μA mA |

Notes: (1) Pulse test: 300μs pulse width, 1% duty cycle

(2) PCB mounted

SS3H9 and SS3H10



Vishay Semiconductors
formerly General Semiconductor

Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Fig. 1 – Forward Current Derating Curve

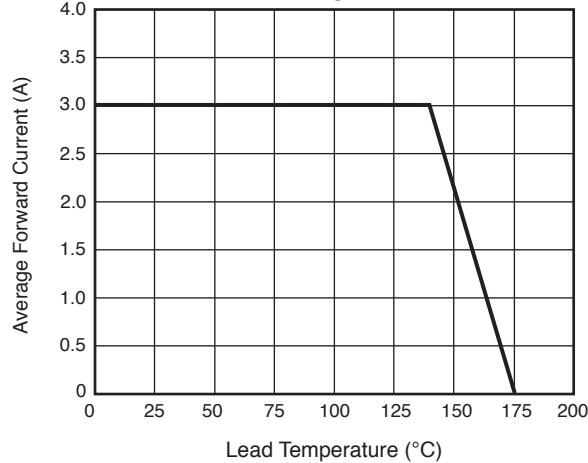


Fig. 3 – Typical Instantaneous Forward Characteristics

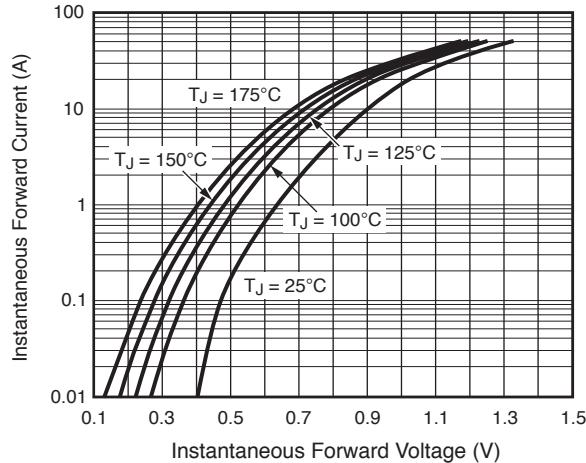


Fig. 5 – Typical Junction Capacitance

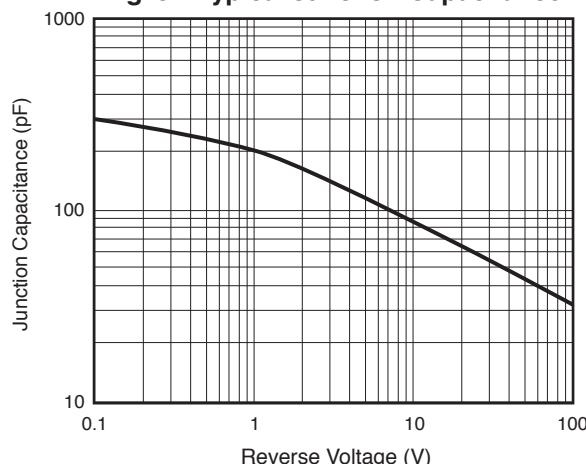


Fig. 2 – Maximum Non-repetitive Peak Forward Surge Current

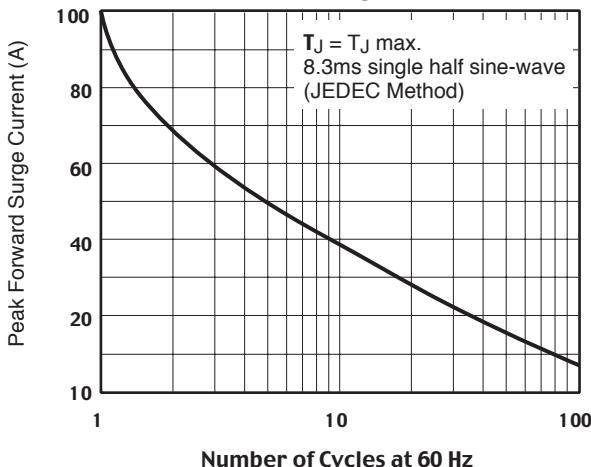


Fig. 4 – Typical Reverse Characteristics

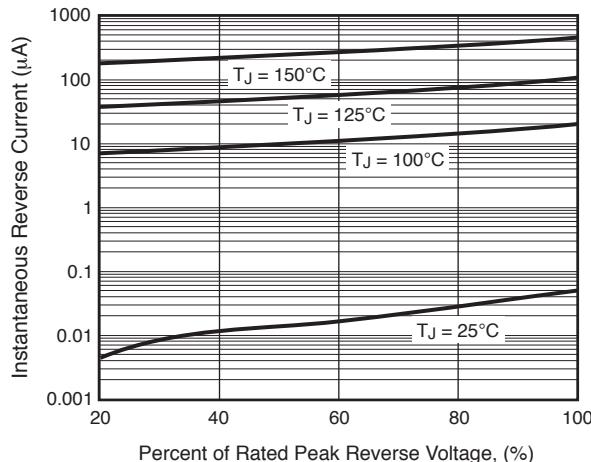


Fig. 6 – Typical Transient Thermal Impedance

